

Introduction

Project title: **Ultra-high Charge Carrier Mobility to Elucidate Transport Mechanisms in Molecular Semiconductors (UHMb)**

Substrate induced polymorphism: Origin, stability and applicability (ESR 8)

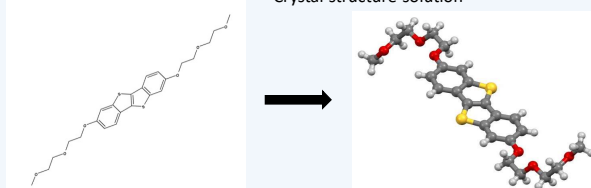
Goal: Organic semiconductor-based devices with improved charge transport properties

Methodology: Structure-Property relationship

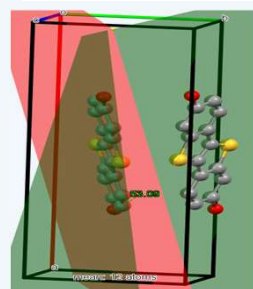
Area of Investigation: 1) Design and synthesis of novel organic semiconductors
 2) Charge transport studies
 3) Discovery of new polymorphs

Molecule of Interest: OEG-BTBT-OEG

- Crystal structure solution



a	18.635
b	7.6670
c	8.2930
α	90
β	99.35
γ	90
Volume	1169.14
Z	2
Crystal density	1.354 g/cm ³
Temperature	298K



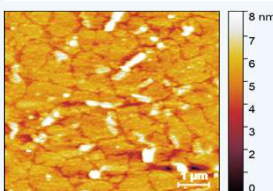
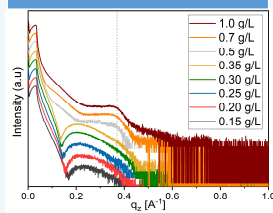
Herring bone angle = 53°

Thin film-forming properties

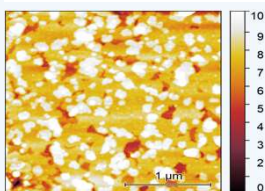
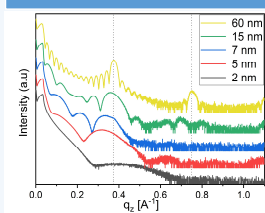
- Mono to bulk layer

Thin film

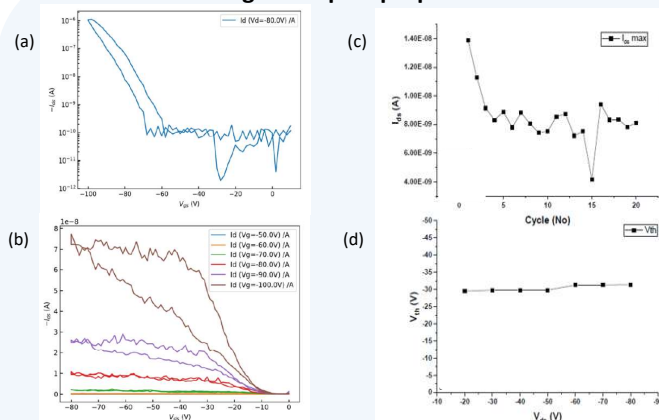
Solution processing (spin coating)



Physical vapor deposition (thermal evaporation)

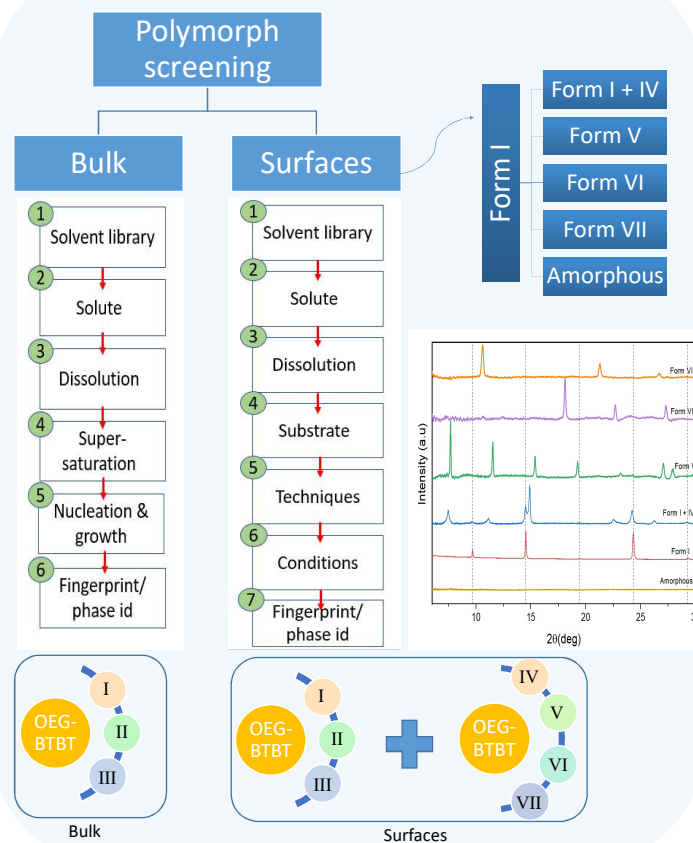


Charge transport properties



(a) Transfer and (b) output characteristics of OEG-BTBT based OFET device, (c) Maximum drain current of FD44 based transistor upon repetitive recording of transfer characteristics ($V_g = -40$ V, $V_d = -10$ V), (d) evolution of threshold voltage upon increasing V_{ds} ($V_g = -40$ V)

Discovering polymorphs



Conclusions

- Solved crystal structure of OEG-BTBT (Form I).
- Thin film forming properties of OEG-BTBT was investigated for solution processed and physical vapor deposited films.
- Charge transport properties of OEG-BTBT based OTFTs were studied.
- Polymorph screening process was carried out in bulk (3 phases) and at surfaces (4 phases).

Acknowledgement

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